

ASC30N1200MT4

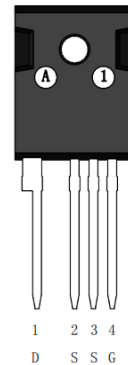
1200V N-Channel MOSFET

Description

Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

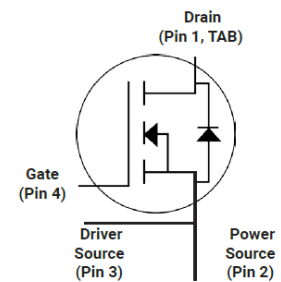
Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Optimized package with separate driver source pin
- Easy to parallel and simple to drive
- ROHS Compliant, Halogen free



Application

- EV Charging
- High Voltage DC/DC Converters
- Switch Mode Power Supplies
- Power Factor Correction Modules



Ordering Information

Part Number	Marking	Package	Packaging
ASC30N1200MT4	ASC30N1200MT4	TO-247-4	Tube

ASC30N1200MT4**1200V N-Channel MOSFET****Absolute Maximum Ratings(Tc=25°C)**

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	1200	V
I_D	Drain Current(continuous)at Tc=25°C	32	A
I_D	Drain Current(continuous)at Tc=100°C	23	A
I_{DM}	Drain Current (pulsed)	80	A
V_{GS}	Gate-Source Voltage	-10/+22	V
P_D	Power Dissipation T _c = 25°C	175	W
T _J , Tstg	Junction and Storage Temperature Range	-55 to +175	°C

Electrical Characteristics(T_J = 25°C unless otherwise specified)**Typical Performance-Static**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-source Breakdown Voltage	$I_D=250\mu A, V_{GS}=0V$	1200			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=1200V, V_{GS}=0V, T_J=25^\circ C$			100	μA
I_{GSS}	Gate-body Leakage Current	$V_{DS}=0V; V_{GS}=-10$ to 20V			250	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=5mA$	2	3	4	V
$V_{GS(on)}$	Recommended turn-on Voltage	Static		18		V
$V_{GS(off)}$	Recommended turn-off Voltage			-5		V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS}=18V, I_D=20A$		80	100	m Ω
		$V_{GS}=18V, I_D=20A$ T _J =175°C		144		m Ω

Typical Performance-Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS}=1000V, f=1MHz,$ $V_{AC}=25mV$		1455		pF
C_{oss}	Output Capacitance			78		pF
C_{rss}	Reverse Transfer Capacitance			3.5		pF
g_{fs}	Transconductance	$V_{DS}=20V, I_D=20A$		2.8		S
E_{OSS}	C_{OSS} Stored Energy	$V_{DS}=1000V, f=1MHz$		35.7		μJ
E_{ON}	Turn-On Energy (Body Diode)	$V_{DS}=800V, V_{GS}=-5/20V,$ $I_D=20A, L=150\mu H$ $T_J=175^\circ C$		495		μJ
E_{OFF}	Turn-Off Energy (Body Diode)			121		μJ
Q_g	Total Gate Charge	$V_{DS}=800V, V_{GS}=-5V/20V,$ $I_D = 15 A$		72		nC
Q_{gs}	Gate-source Charge			21		nC
Q_{gd}	Gate-Drain Charge			22		nC
$R_{G(int)}$	Internal Gate Resistance	$f=1MHz, V_{AC}=25mV$		5.6		Ω
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=800V, V_{GS}=-5V/20V,$ $I_D = 20A, L=150 \mu H$ $R_{ext}=2.5\Omega$		42		ns
t_r	Rise Time			15		ns
$t_{d(off)}$	Turn-off Delay Time			36		ns
t_f	Fall Time			11		ns

Typical Performance-Reverse Diode($T_J = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{FSD}	Forward Voltage	$V_{GS}=0V, I_F=10A, T_J=25^\circ C$		3.9	6	V
		$V_{GS}=0V, I_F=10A, T_J=175^\circ C$		3.5	6	V
I_S	Continuous Diode Forward Current	$V_{GS}=0V, T_C=25^\circ C$		27		A
t_{rr}	Reverse Recovery Time	$V_{GS}=-5 V, I_F=20A,$ $V_R=800 V, di/dt=900$ $A/\mu s, T_J=175^\circ C$		36		nS
Q_{rr}	Reverse Recovery Charge			297		nC
I_{rrm}	Peak Reverse Recovery Current			15.5		A

Thermal Characteristics

Symbol	Parameter	Value.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.86	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	40	$^\circ C/W$

The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of $T_J(max)=175^\circ C$

Electrical Characteristics

Fig1. Output characteristics ($T_J = 25^\circ\text{C}$)

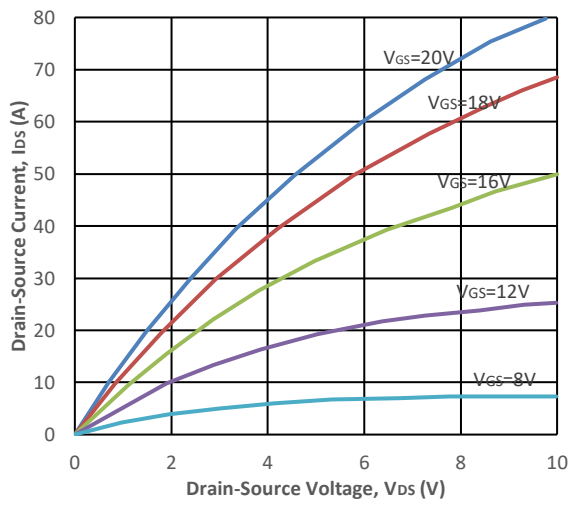


Fig2. Output characteristics ($T_J = 175^\circ\text{C}$)

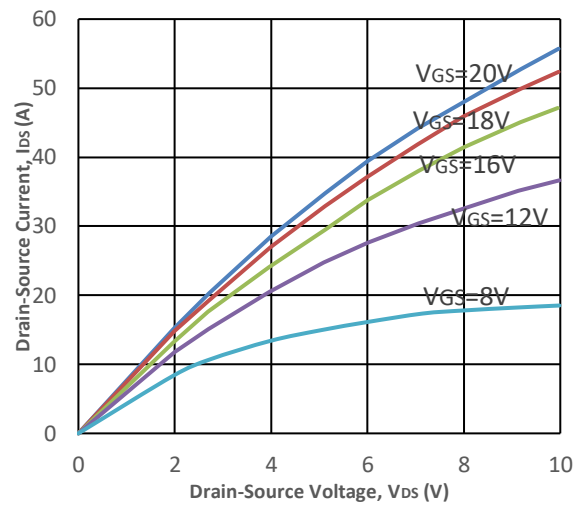


Fig3. Normalized On-Resistance vs. Temperature

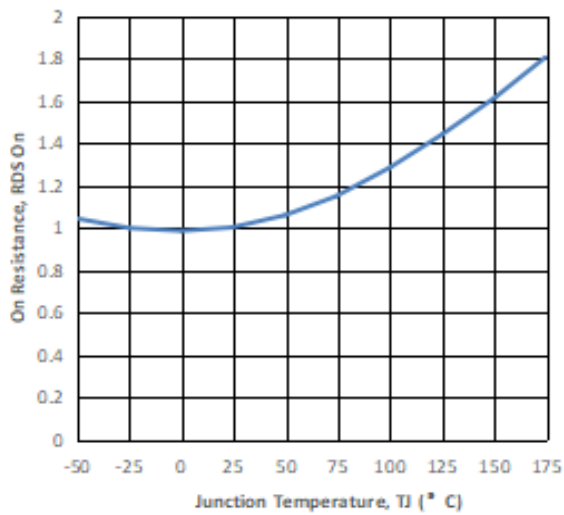


Fig4. On-Resistance vs. Temperature

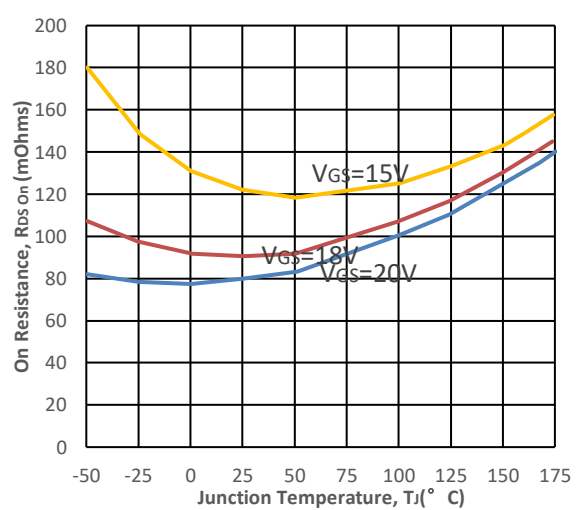


Fig5. Transfer Characteristic

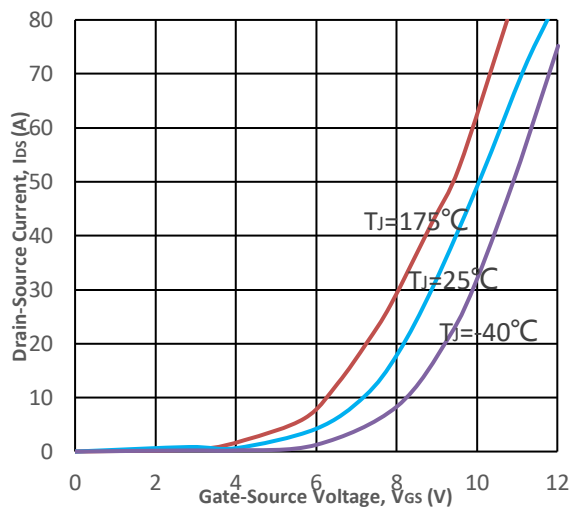


Fig6. Body Diode Characteristic at 25°C

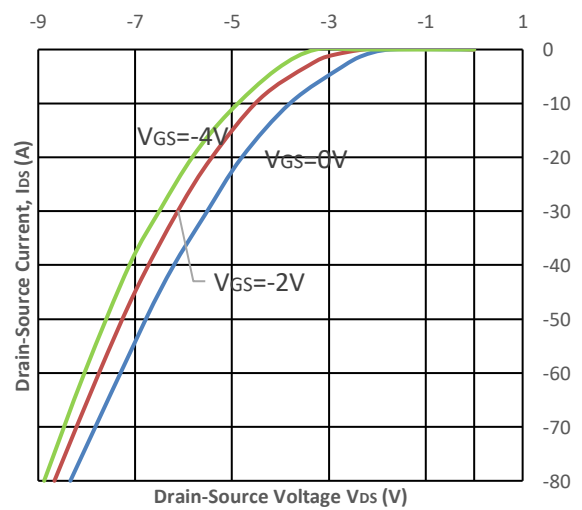


Fig7. Threshold Voltage vs. Temperature

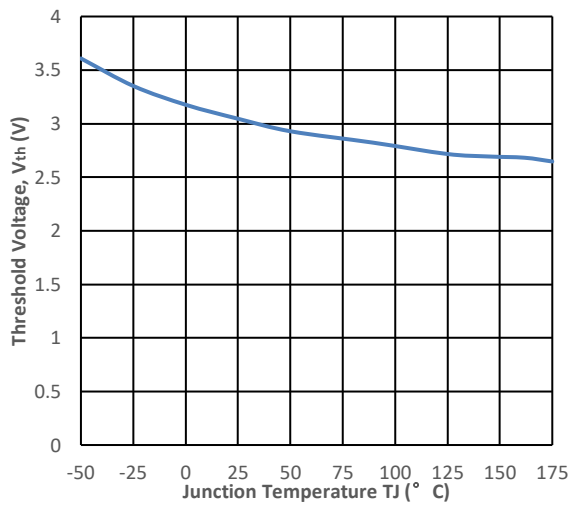


Fig8. Gate Charge Characteristics

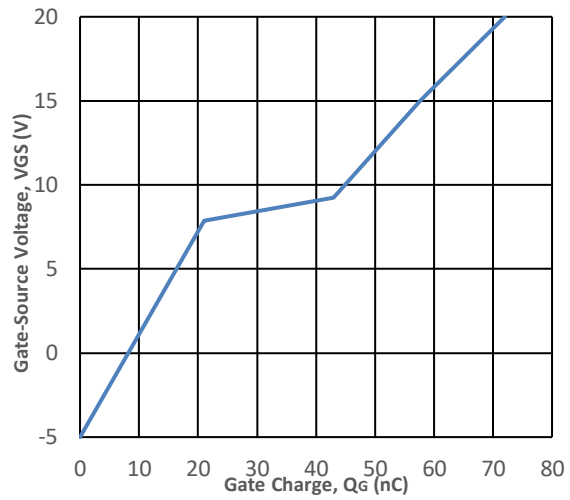


Fig9. 3rd Quadrant Characteristic at 25 °C

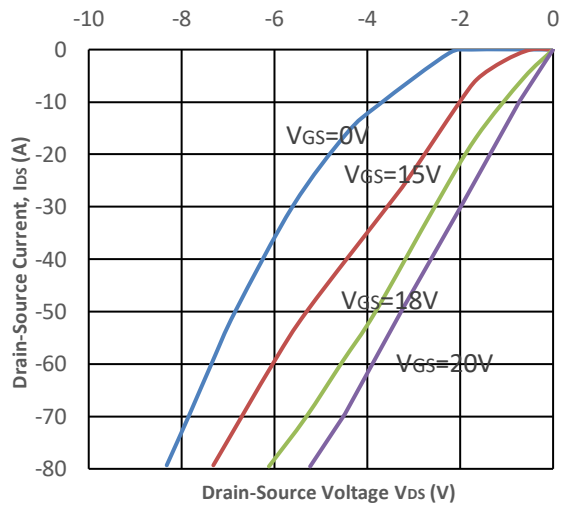


Fig10. Output Capacitor Stored Energy

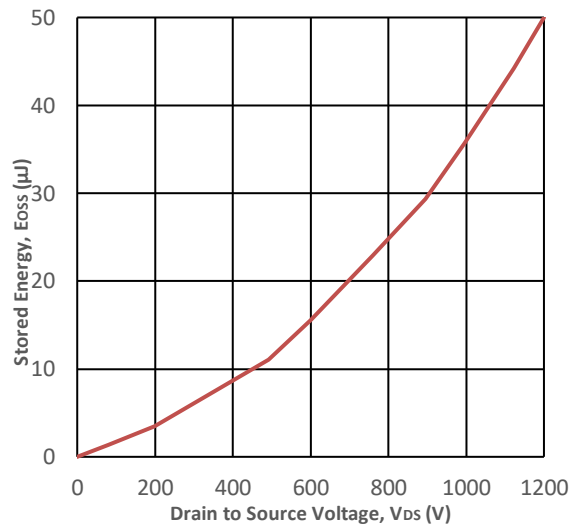


Fig11. Capacitances vs. Drain-Source

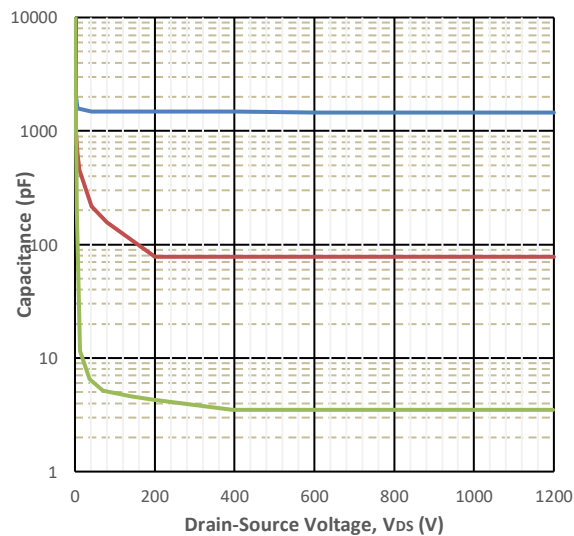


Fig12. Max Power Dissipation Derating Vs T_c

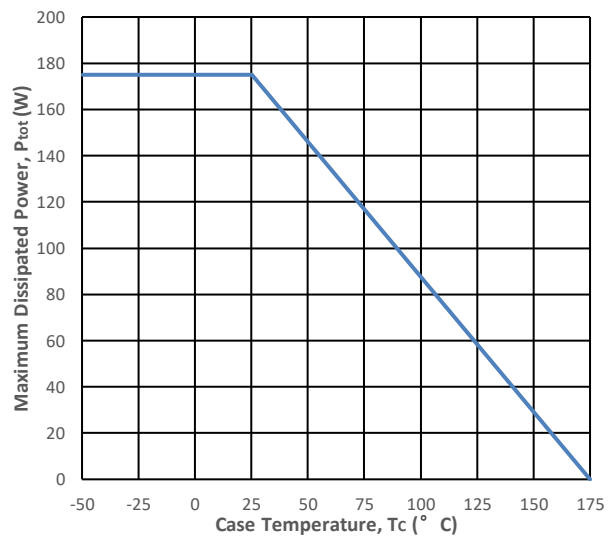


Fig13. Switching Energy vs. Drain Current

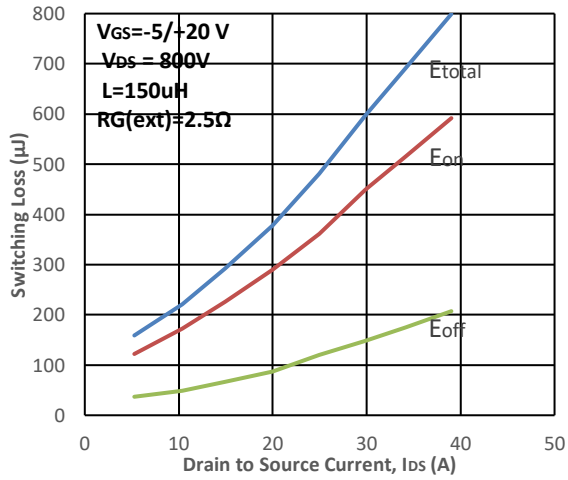


Fig14. Switching Energy vs. $R_{G(\text{ext})}$

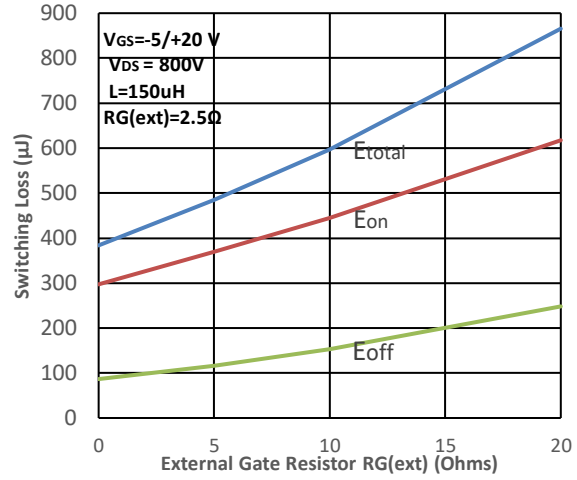


Fig15. Switching Energy vs. Temperature

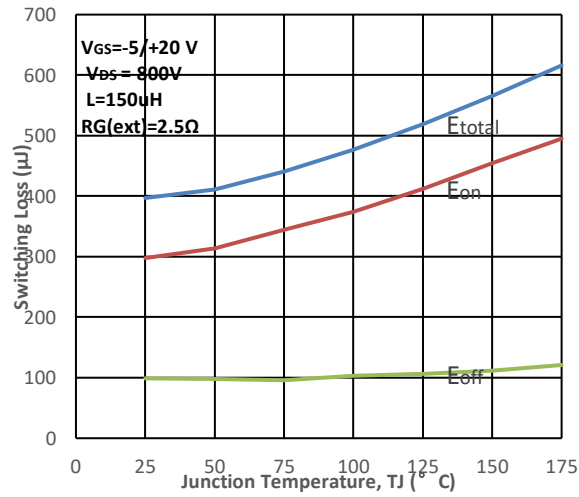


Fig16. Switching Times vs. $R_{G(\text{ext})}$

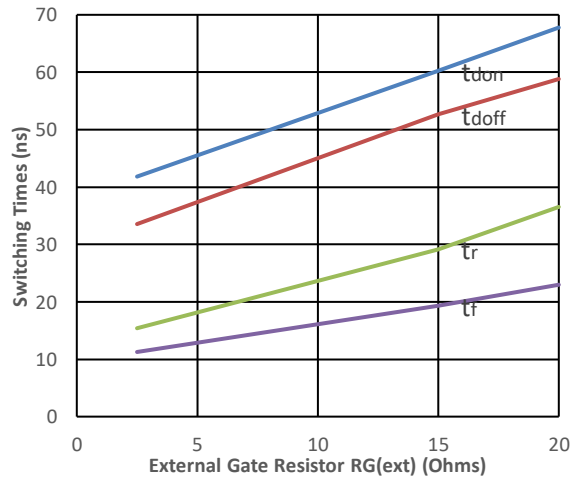


Fig17. Transient Thermal Impedance

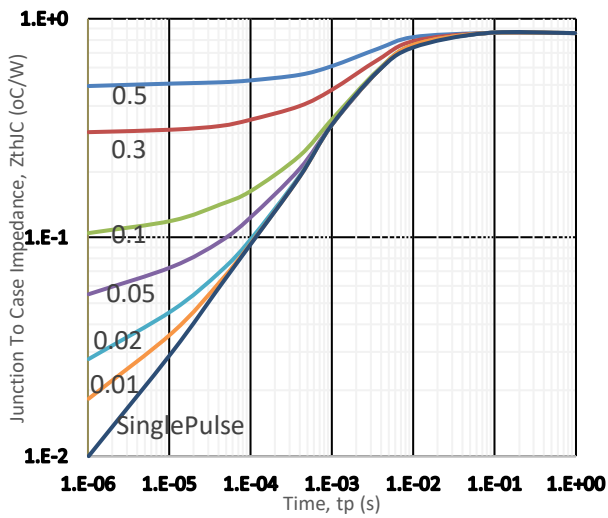
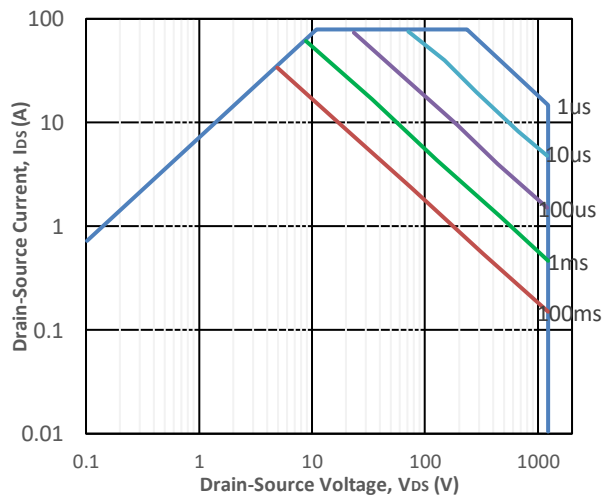
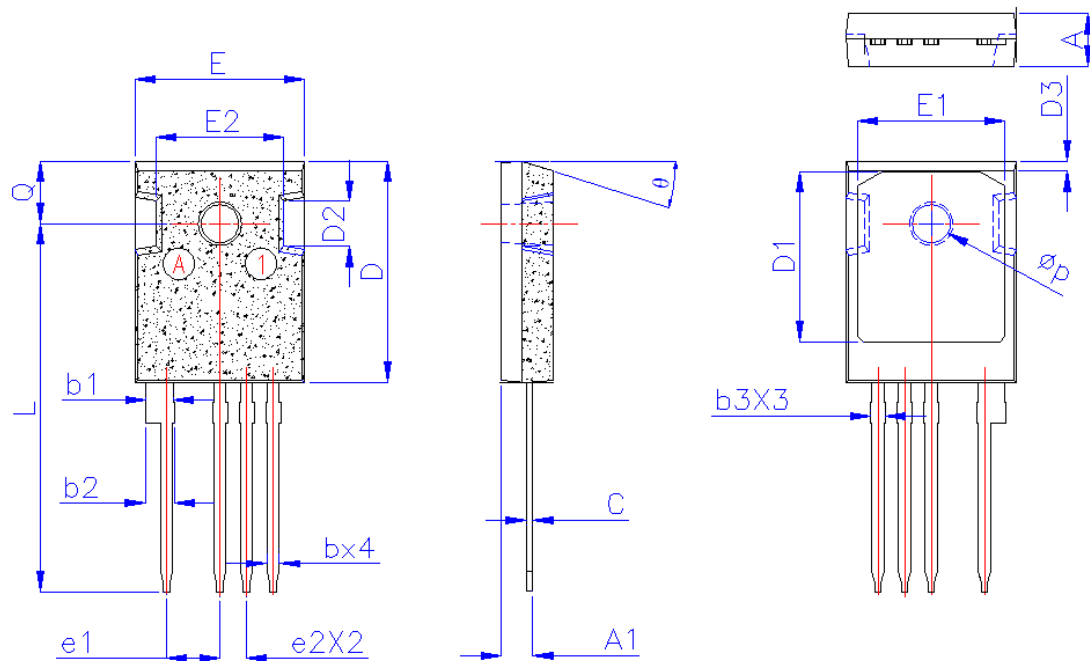


Fig18. Safe Operating Area



Package Drawing:



Dimensions (UNIT: mm)

SYMBDLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	TYPE	MAX	MIN	TYPE	MAX
A	4.80	5.00	5.20	0.189	0.197	0.205
A1	2.85	3.00	3.15	0.112	0.118	0.124
b	1.15	1.20	1.25	0.045	0.047	0.049
b1	2.40	2.50	2.60	0.094	0.098	0.102
b2	2.61	2.76	2.91	0.103	0.109	0.115
b3	1.30	1.42	1.57	0.051	0.056	0.062
C	0.55	0.60	0.65	0.022	0.024	0.026
D	20.80	21.00	21.20	0.819	0.827	0.835
D1	15.94	16.24	16.54	0.628	0.639	0.651
D2	4.3 TYPE			0.169 TYPE		
e1	4.93	5.08	5.23	0.194	0.200	0.206
e2	2.39	2.54	2.69	0.094	0.100	0.106
E	15.95	16.15	16.35	0.628	0.636	0.644
E1	13.82	14.02	14.26	0.544	0.552	0.561
E2	12.00	12.20	12.40	0.472	0.480	0.488
L	34.65	35.05	35.45	1.364	1.380	1.396
Q	5.85	5.95	6.05	0.230	0.234	0.238
øP	3.45	3.60	3.75	0.136	0.142	0.148
θ	17.5°			0.689°		

Notes:

- The information in this document is subject to change without notice.
- For more product and company information please contact us or visit the website.

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